

36. (Amended) A semiconductor device claimed in Claim 35, wherein said refractory conductive material covers a sidewall surface of said large diameter contact hole to a predetermined distance in the range of not less than 10% but not greater than 40% of a thickness of said insulator film.

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37. (Amended) A semiconductor device claimed in Claim 34, wherein said refractory conductive material covers a sidewall surface of said large diameter contact hole to a predetermined distance in the range of not less than 10% but not greater than 40% of a thickness of said insulator film.

41. (Amended) A semiconductor device claimed in Claim 40, wherein said refractory conductive material covers a sidewall surface of said large diameter contact hole to a predetermined distance in the range of not less than 10% but not greater than 40% of a thickness of said insulator film.

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42. (Amended) A semiconductor device claimed in Claim 38, wherein said refractory conductive material covers a sidewall surface of said large diameter contact hole to a predetermined distance in the range of not less than 10% but not greater than 40% of a thickness of said insulator film.

45. (Amended) A semiconductor device claimed in Claim 44, wherein said refractory conductive material covers a sidewall surface of said large diameter contact hole to a predetermined distance in the range of not less than 10% but not greater than 40% of a thickness of said insulator film.

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46. (Amended) A semiconductor device claimed in Claim 43, wherein said refractory conductive material covers a sidewall surface of said large diameter contact hole to a